CLAIMS

1. A surface treatment composition comprising a first surfactant, a second surfactant, a basic compound, and water, the surface treatment composition having a pH of 8 or more, wherein the second surfactant has a weight-average molecular weight one-half or less that of the first surfactant, and the sum of a content of the first surfactant and a content of the second surfactant is 0.00001 to 0.1% by mass.

2. The surface treatment composition according to claim 1, wherein a ratio of a total number of carbon atoms of the second surfactant to a sum of a total number of carbon atoms of the first surfactant and the total number of carbon atoms of the second surfactant is 1 to 90%.

3. The surface treatment composition according to claim 1 or 2, wherein the first surfactant has a weight-average molecular weight of 500 to 20,000.

4. The surface treatment composition according to any one of claims 1 to 3, wherein both the first surfactant and the second surfactant are non-ionic surfactants.

5. The surface treatment composition according to any one of claims 1 to 4, further comprising a particle component.

6. The surface treatment composition according to claim 5, wherein the particle component is silicon dioxide.

7. The surface treatment composition according to any one of claims 1 to 6, further comprising a wetting agent.

8. The surface treatment composition according to any one of claims 1 to 7, wherein the surface treatment composition is

used in an application of subjecting a silicon wafer to surface treatment.

9. The surface treatment composition according to any one of claims 1 to 7, wherein the surface treatment composition is used in an application of polishing or rinsing a surface of a substrate.

10. A kit for preparing the surface treatment composition according to any one of claims 1 to 9, the kit comprising a first surfactant, a second surfactant having a weight-average molecular weight one-half or less that of the first surfactant, and a basic compound.

11. A surface treatment method comprising polishing, washing, rinsing, or etching a surface of a substrate using the surface treatment composition according to any one of claims 1 to 7.

12. A surface treatment method comprising polishing or rinsing a surface of a substrate using the surface treatment composition according to any one of claims 1 to 7.

13. The surface treatment method according to claim 11 or 12, wherein the substrate is a silicon wafer.

CLAIMS

1. A surface treatment composition comprising a first surfactant, a second surfactant, a basic compound, and water, the surface treatment composition having a pH of 8 or more,

wherein the second surfactant has a weight-average molecular weight 1/2 times or less that of the first surfactant, and the sum of a content of the first surfactant and a content of the second surfactant is 0.00001 to 0.1% by mass, and

wherein both the first surfactant and the second surfactant are nonionic surfactants.

2. The surface treatment composition according to claim 1, wherein a ratio of a total number of carbon atoms of the second surfactant to a sum of a total number of carbon atoms of the first surfactant and the total number of carbon atoms of the second surfactant is 1 to 90%.

3. The surface treatment composition according to claim 1 or 2, wherein the first surfactant has a weight-average molecular weight of 500 to 20,000.

4. The surface treatment composition according to any one of claims 1 to 3, further comprising a particle component.

5. The surface treatment composition according to claim 4, wherein the particle component is silicon dioxide.

6. The surface treatment composition according to any one of claims 1 to 5, further comprising a wetting agent.

7. The surface treatment composition according to any one of claims 1 to 6, wherein the surface treatment composition is used in an application of subjecting a silicon wafer to surface treatment.

8. The surface treatment composition according to any one of claims 1 to 6, wherein the surface treatment composition is used in an application of polishing or rinsing a surface of a substrate.

9. A surface treatment method comprising polishing, washing, rinsing, or etching a surface of a substrate using the surface treatment composition according to any one of claims 1 to 6.

10. A surface treatment method comprising polishing or rinsing a surface of a substrate using the surface treatment composition according to any one of claims 1 to 6.

11. The surface treatment method according to claim 9 or 10, wherein the substrate is a silicon wafer.